500 mW DO-35 Hermetically Sealed Glass Zener Voltage Regulators

This is a complete series of 500 mW Zener diodes with limits and excellent operating characteristics that reflect the superior capabilities of silicon–oxide passivated junctions. All this in an axial–lead hermetically sealed glass package that offers protection in all common environmental conditions.

Specification Features:

- Zener Voltage Range 1.8 V to 27 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- DO–204AH (DO–35) Package Smaller than Conventional DO–204AA Package
- Double Slug Type Construction
- Metallurgical Bonded Construction

Mechanical Characteristics:

CASE: Double slug type, hermetically sealed glass **FINISH:** All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:

230°C, 1/16" from the case for 10 seconds **POLARITY:** Cathode indicated by polarity band **MOUNTING POSITION:** Any

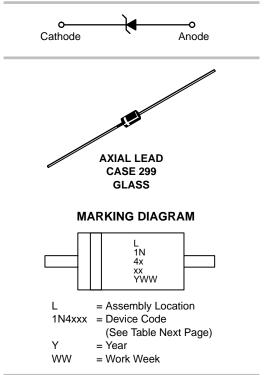
| MAXIMUM RATINGS (Note 1.) | | | |
|---|-----------------------------------|----------------|-------|
| Rating | Symbol | Value | Unit |
| Max. Steady State Power Dissipation @ $T_1 \le 75^{\circ}$ C, Lead Length = 3/8" | PD | 500 | mW |
| Derate above 75°C | | 4.0 | mW/°C |
| Operating and Storage Temperature Range | T _J , T _{stg} | -65 to +200 | °C |

1. Some part number series have lower JEDEC registered ratings.



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ORDERING INFORMATION

| Device | Package | Shipping |
|------------------------|------------|------------------|
| 1N4xxx | Axial Lead | 3000 Units/Box |
| 1N4xxxRL | Axial Lead | 5000/Tape & Reel |
| 1N4xxxRL2 * | Axial Lead | 5000/Tape & Reel |
| 1N4xxxTA | Axial Lead | 5000/Ammo Pack |
| 1N4xxxTA2 * | Axial Lead | 5000/Tape & Reel |
| 1N4xxxRR1 [†] | Axial Lead | 3000/Tape & Reel |
| 1N4xxxRR2 [‡] | Axial Lead | 3000/Tape & Reel |

* The "2" suffix refers to 26 mm tape spacing.

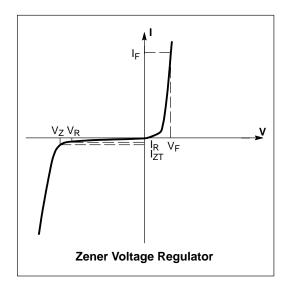
[†] Polarity band **up** with cathode lead off first

[‡] Polarity band **down** with cathode lead off first

Devices listed in *bold, italic* are ON Semiconductor **Preferred** devices. **Preferred** devices are recommended choices for future use and best overall value. Low level oxide passivated zener diodes for applications requiring extremely low operating currents, low leakage, and sharp breakdown voltage.

| ELECTRICAL CHARACTERISTICS (T _A = 25°C unless |
|--|
| otherwise noted, $V_F = 1.5 V Max @ I_F = 100 mA$ for all types) |

| Symbol | Parameter | | | |
|-----------------|--|--|--|--|
| Vz | Reverse Zener Voltage @ I _{ZT} | | | |
| I _{ZT} | Reverse Current | | | |
| ΔV_Z | Reverse Zener Voltage Change | | | |
| I _{ZM} | Maximum Zener Current | | | |
| I _R | Reverse Leakage Current @ V _R | | | |
| V _R | Breakdown Voltage | | | |
| ١ _F | Forward Current | | | |
| V _F | Forward Voltage @ I _F | | | |



| | | Zener Voltage (Note 3.) | | | Leakage Current (Note 4.) | | I _{ZM} | ΔVz | |
|-----------|---------|-------------------------|------------------------|-------|---------------------------|---------------------------------|-----------------|-----------|----------|
| Device | Device | | V _Z (Volts) | | @ ել | I _R @ V _R | | (Note 5.) | (Note 6. |
| (Note 2.) | Marking | Min | Nom | Мах | μΑ | μ Α Μax | Volts | mA | Volts |
| 1N4678 | 1N4678 | 1.71 | 1.8 | 1.89 | 50 | 7.5 | 1 | 120 | 0.7 |
| 1N4679 | 1N4679 | 1.9 | 2.0 | 2.1 | 50 | 5 | 1 | 110 | 0.7 |
| 1N4680 | 1N4680 | 2.09 | 2.2 | 2.31 | 50 | 5 | 1 | 100 | 0.75 |
| 1N4681 | 1N4681 | 2.28 | 2.4 | 2.52 | 50 | 2 | 1 | 95 | 0.8 |
| 1N4682 | 1N4682 | 2.565 | 2.7 | 2.835 | 50 | 1 | 1 | 90 | 0.85 |
| 1N4683 | 1N4683 | 2.85 | 3.0 | 3.15 | 50 | 0.8 | 1 | 85 | 0.9 |
| 1N4684 | 1N4684 | 3.135 | 3.3 | 3.465 | 50 | 7.5 | 1.5 | 80 | 0.95 |
| 1N4685 | 1N4685 | 3.42 | 3.6 | 3.78 | 50 | 7.5 | 2 | 75 | 0.95 |
| 1N4686 | 1N4686 | 3.705 | 3.9 | 4.095 | 50 | 5.0 | 2 | 70 | 0.97 |
| 1N4687 | 1N4687 | 4.085 | 4.3 | 4.515 | 50 | 4.0 | 2 | 65 | 0.99 |
| 1N4688 | 1N4688 | 4.465 | 4.7 | 4.935 | 50 | 10 | 3 | 60 | 0.99 |
| 1N4689 | 1N4689 | 4.845 | 5.1 | 5.355 | 50 | 10 | 3 | 55 | 0.97 |
| 1N4690 | 1N4690 | 5.32 | 5.6 | 5.88 | 50 | 10 | 4 | 50 | 0.96 |
| 1N4691 | 1N4691 | 5.89 | 6.2 | 6.51 | 50 | 10 | 5 | 45 | 0.95 |
| 1N4692 | 1N4692 | 6.46 | 6.8 | 7.14 | 50 | 10 | 5.1 | 35 | 0.9 |
| 1N4693 | 1N4693 | 7.125 | 7.5 | 7.875 | 50 | 10 | 5.7 | 31.8 | 0.75 |
| 1N4694 | 1N4694 | 7.79 | 8.2 | 8.61 | 50 | 1 | 6.2 | 29 | 0.5 |
| 1N4695 | 1N4695 | 8.265 | 8.7 | 9.135 | 50 | 1 | 6.6 | 27.4 | 0.1 |
| 1N4696 | 1N4696 | 8.645 | 9.1 | 9.555 | 50 | 1 | 6.9 | 26.2 | 0.08 |
| 1N4697 | 1N4697 | 9.5 | 10 | 10.5 | 50 | 1 | 7.6 | 24.8 | 0.1 |
| 1N4698 | 1N4698 | 10.45 | 11 | 11.55 | 50 | 0.05 | 8.4 | 21.6 | 0.11 |
| 1N4699 | 1N4699 | 11.4 | 12 | 12.6 | 50 | 0.05 | 9.1 | 20.4 | 0.12 |
| 1N4700 | 1N4700 | 12.35 | 13 | 13.65 | 50 | 0.05 | 9.8 | 19 | 0.13 |
| 1N4701 | 1N4701 | 13.3 | 14 | 14.7 | 50 | 0.05 | 10.6 | 17.5 | 0.14 |
| 1N4702 | 1N4702 | 14.25 | 15 | 15.75 | 50 | 0.05 | 11.4 | 16.3 | 0.15 |
| 1N4703 | 1N4703 | 15.2 | 16 | 16.8 | 50 | 0.05 | 12.1 | 15.4 | 0.16 |
| 1N4704 | 1N4704 | 16.15 | 17 | 17.85 | 50 | 0.05 | 12.9 | 14.5 | 0.17 |
| 1N4705 | 1N4705 | 17.1 | 18 | 18.9 | 50 | 0.05 | 13.6 | 13.2 | 0.18 |
| 1N4707 | 1N4707 | 19 | 20 | 21 | 50 | 0.01 | 15.2 | 11.9 | 0.2 |
| 1N4711 | 1N4711 | 25.65 | 27 | 28.35 | 50 | 0.01 | 20.4 | 8.8 | 0.27 |

ELECTRICAL CHARACTERISTICS (T_L = 30°C unless otherwise noted, V_F = 1.5 V Max @ I_F = 100 mA for all types)

2. TOLERANCE AND TYPE NUMBER DESIGNATION (V_Z) The type numbers listed have a standard tolerance of $\pm 5\%$ on the nominal zener voltage.

ZENER VOLTAGE (V_Z) MEASUREMENT

The zener voltage is measured with the device junction in the thermal equilibrium at the lead temperature (T_L) at 30°C ± 1°C and 3/8″ lead length.

4. **REVERSE LEAKAGE CURRENT (I**_R) Reverse leakage currents are guaranteed and measured at V_R shown on the table.

 MAXIMUM ZENER CURRENT RATINGS (I_{ZM}) Maximum zener current ratings are based on maximum zener voltage of the individual units and JEDEC 250 mW rating.

6. MAXIMUM VOLTAGE CHANGE (ΔV_Z)

Voltage change is equal to the difference between V_Z at 100 μ A and at 10 μ A.

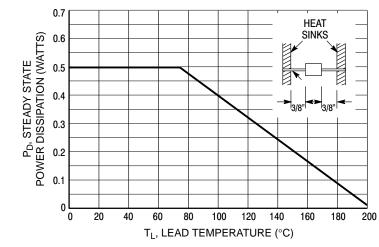


Figure 1. Steady State Power Derating

APPLICATION NOTE — ZENER VOLTAGE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_{L} = \theta_{LA} P_{D} + T_{A}.$$

 θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to 40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L , the junction temperature may be determined by:

$$\mathsf{T}_{\mathsf{J}} = \mathsf{T}_{\mathsf{L}} + \Delta \mathsf{T}_{\mathsf{J}\mathsf{L}}.$$

 ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 2 for dc power:

$$\Delta T_{JL} = \theta_{JL} P_D.$$

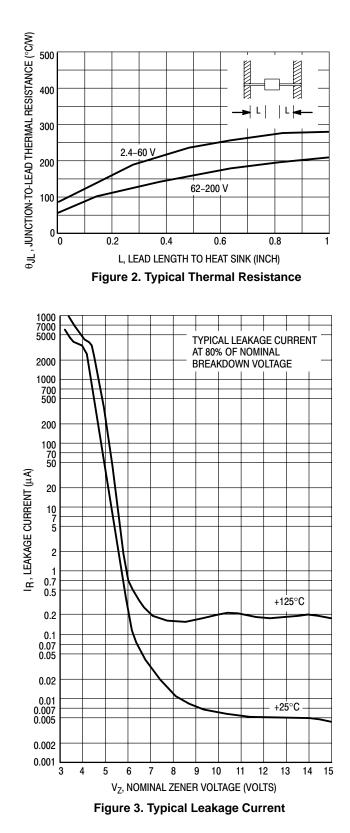
For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta \mathsf{V} = \theta_{\mathsf{VZ}}\mathsf{T}_{\mathsf{J}}.$$

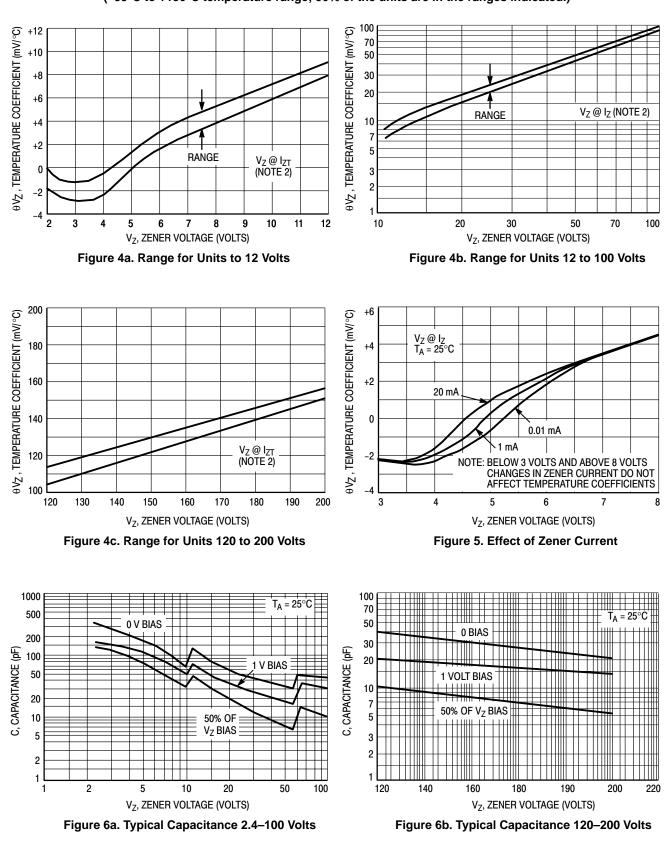
 $\theta_{VZ},$ the zener voltage temperature coefficient, is found from Figures 4 and 5.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 7. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 7 be exceeded.







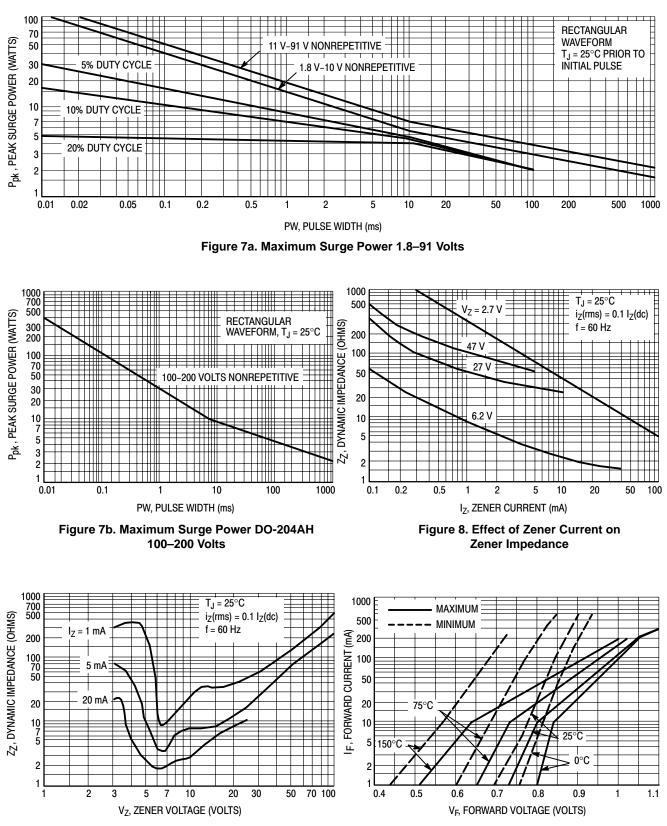
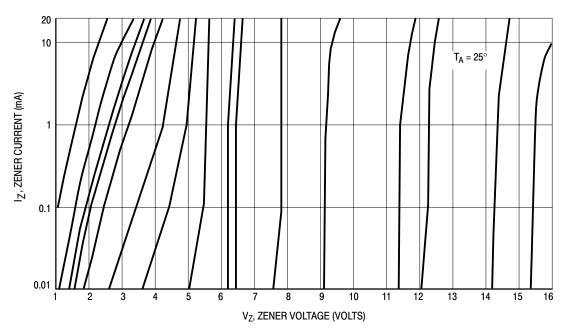
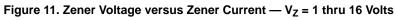


Figure 9. Effect of Zener Voltage on Zener Impedance

Figure 10. Typical Forward Characteristics





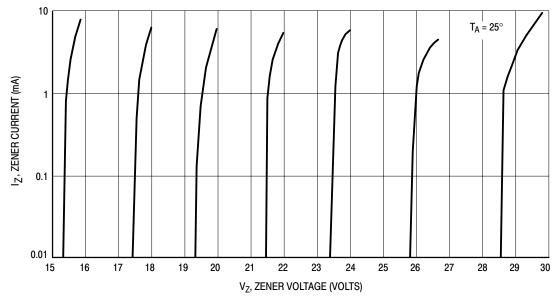


Figure 12. Zener Voltage versus Zener Current — V_Z = 15 thru 30 Volts

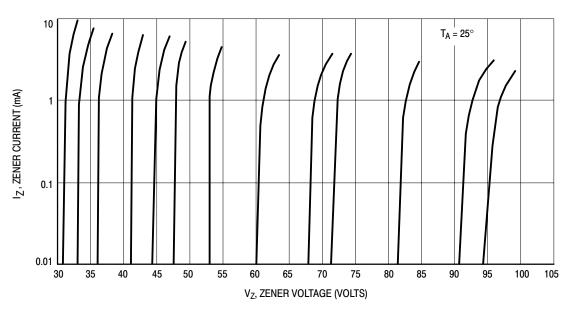


Figure 13. Zener Voltage versus Zener Current — $V_Z = 30$ thru 105 Volts

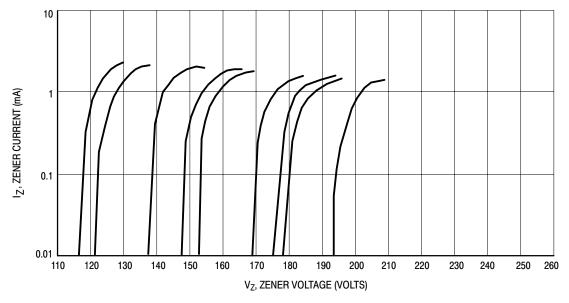


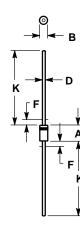
Figure 14. Zener Voltage versus Zener Current — V_Z = 110 thru 220 Volts

OUTLINE DIMENSIONS

Zener Voltage Regulators – Axial Leaded

500 mW DO-35 Glass

GLASS DO-35/D0-204AH CASE 299-02 **ISSUE A**



NOTES:

- NOTES: 1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B. 2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS. 3. POLARITY DEMOTED BY CATHODE BAND
- 3. POLARITY DENOTED BY CATHODE BAND. 4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

| | MILLIMETERS | | INCHES | | |
|-----|-------------|-------|--------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 3.05 | 5.08 | 0.120 | 0.200 | |
| В | 1.52 | 2.29 | 0.060 | 0.090 | |
| D | 0.46 | 0.56 | 0.018 | 0.022 | |
| F | | 1.27 | | 0.050 | |
| K | 25.40 | 38.10 | 1.000 | 1.500 | |

All JEDEC dimensions and notes apply.

<u>Notes</u>

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